

2SK2225

Silicon N Channel MOS FET

REJ03G1005-0200
(Previous: ADE-208-140)
Rev.2.00
Sep 07, 2005

Application

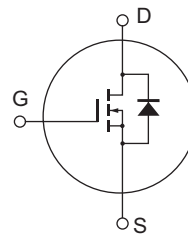
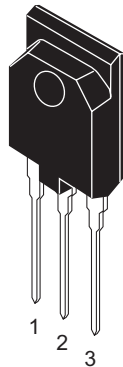
High speed power switching

Features

- High breakdown voltage ($V_{DSS} = 1500\text{ V}$)
- High speed switching
- Low drive current
- No Secondary breakdown
- Suitable for switching regulator, DC-DC converter

Outline

RENESAS Package code: PRSS0003ZA-A
(Package name: TO-3PFM)



1. Gate
2. Drain
3. Source

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	1500	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	2	A
Drain peak current	I _{D(pulse)} * ¹	7	A
Body to drain diode reverse drain current	I _{DR}	2	A
Channel dissipation	P _{ch} * ²	50	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1 %
 2. Value at Tc = 25°C

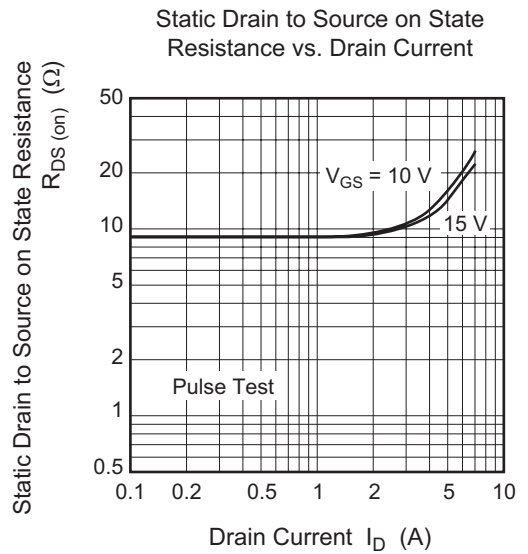
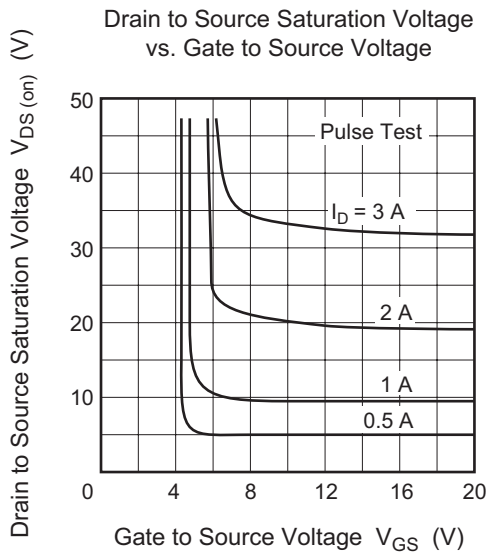
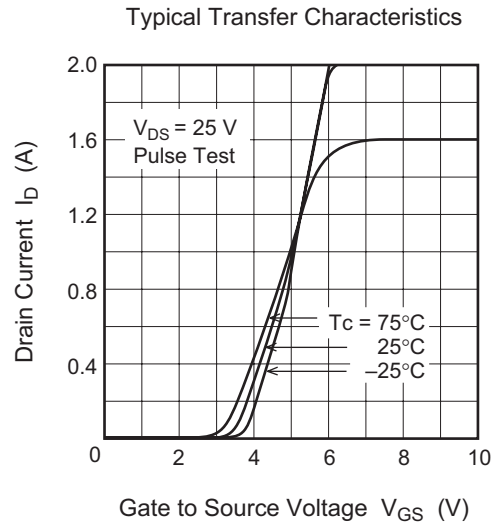
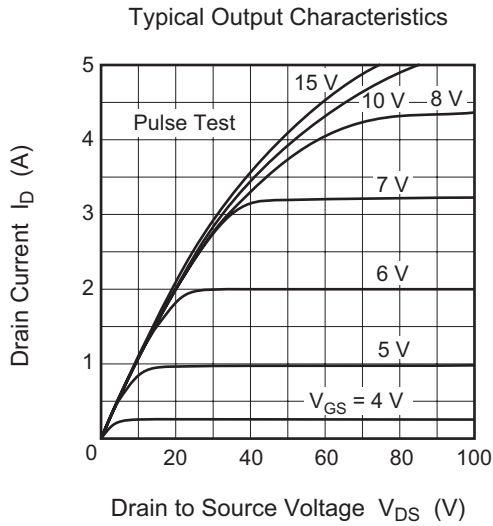
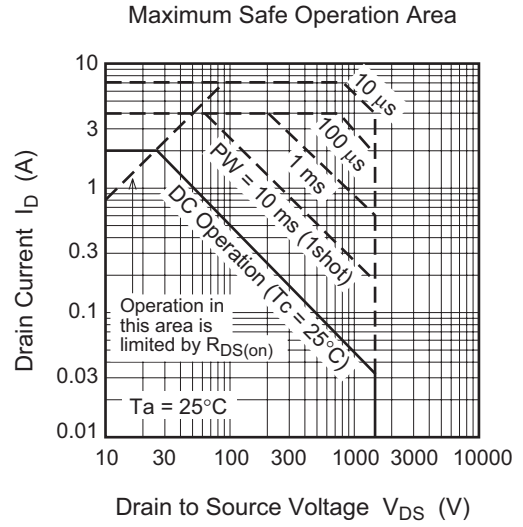
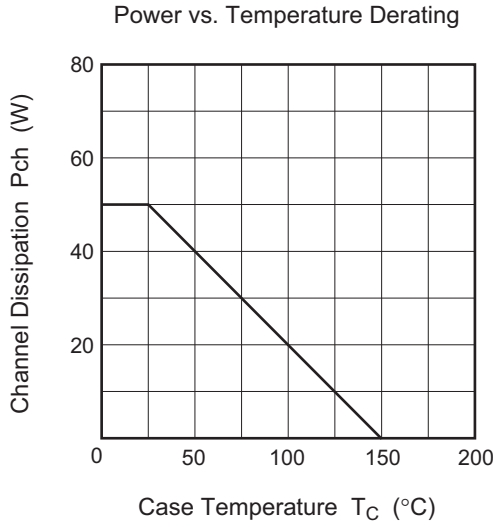
Electrical Characteristics

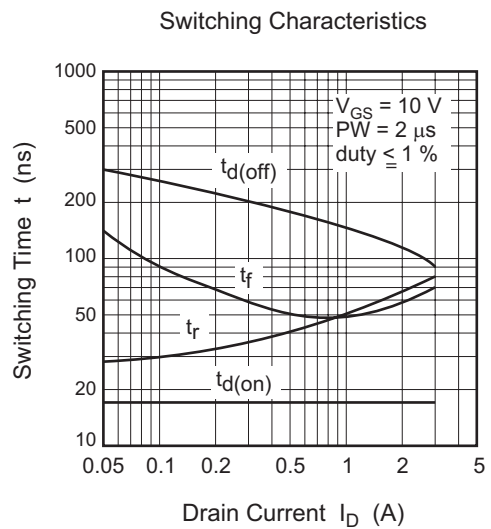
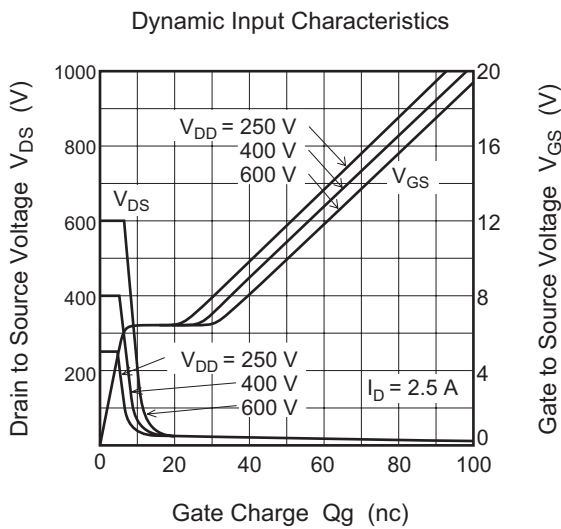
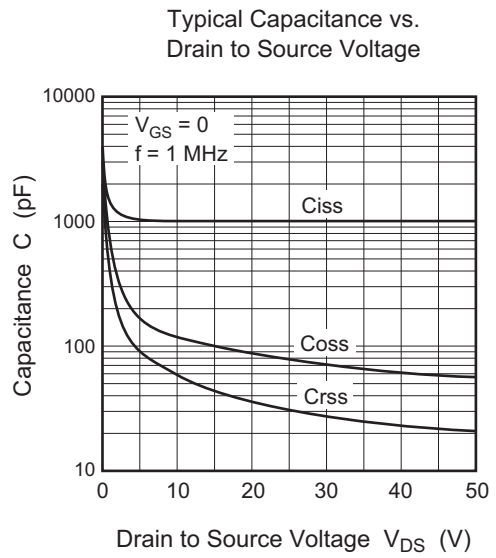
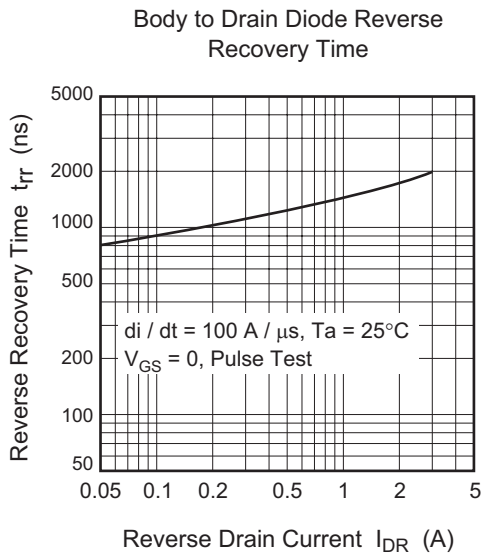
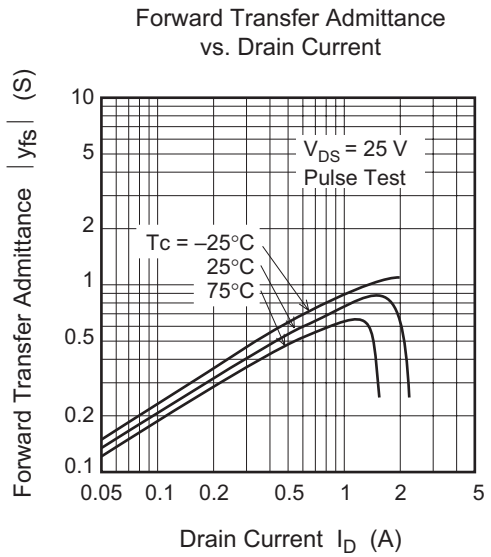
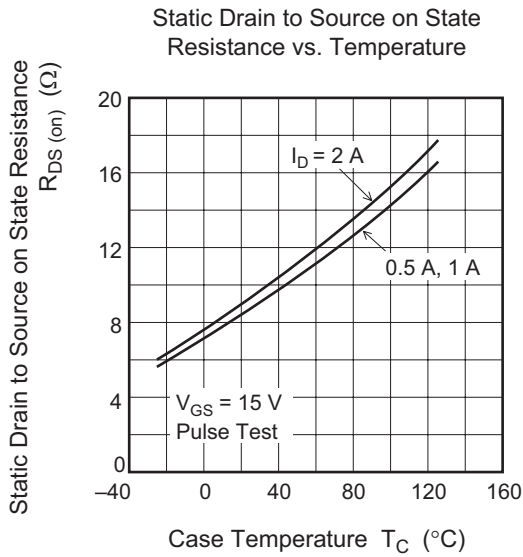
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	1500	—	—	V	I _D = 10 mA, V _{GS} = 0
Gate to source leak current	I _{GSS}	—	—	±1	μA	V _{GS} = ±20 V, V _{DS} = 0
Zero gate voltage drain current	I _{DSS}	—	—	500	μA	V _{DS} = 1200 V, V _{GS} = 0
Gate to source cutoff voltage	V _{GS(off)}	2.0	—	4.0	V	I _D = 1 mA, V _{DS} = 10 V
Static drain to source on state resistance	R _{DS(on)}	—	9	12	Ω	I _D = 1 A, V _{GS} = 15 V* ³
Forward transfer admittance	y _{fs}	0.45	0.75	—	S	I _D = 1 A, V _{DS} = 20 V* ³
Input capacitance	C _{iss}	—	990	—	pF	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz
Output capacitance	C _{oss}	—	125	—	pF	
Reverse transfer capacitance	C _{rss}	—	60	—	pF	
Turn-on delay time	t _{d(on)}	—	17	—	ns	I _D = 1 A, V _{GS} = 10 V, R _L = 30 Ω
Rise time	t _r	—	50	—	ns	
Turn-off delay time	t _{d(off)}	—	150	—	ns	
Fall time	t _f	—	50	—	ns	
Body to drain diode forward voltage	V _{DF}	—	0.9	—	V	I _F = 2 A, V _{GS} = 0
Body to drain diode reverse recovery time	t _{rr}	—	1750	—	ns	I _F = 20 A, V _{GS} = 0, di _F / dt = 100 A / μs

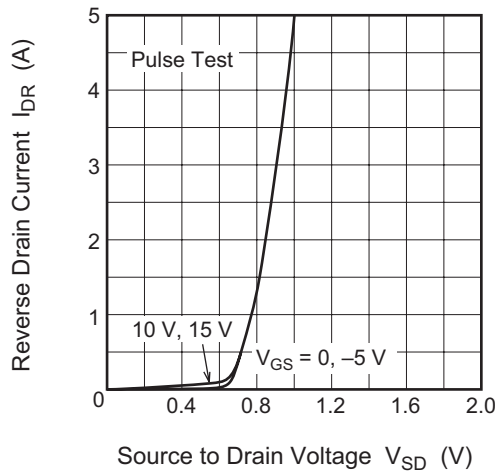
Note: 3. Pulse Test

Main Characteristics

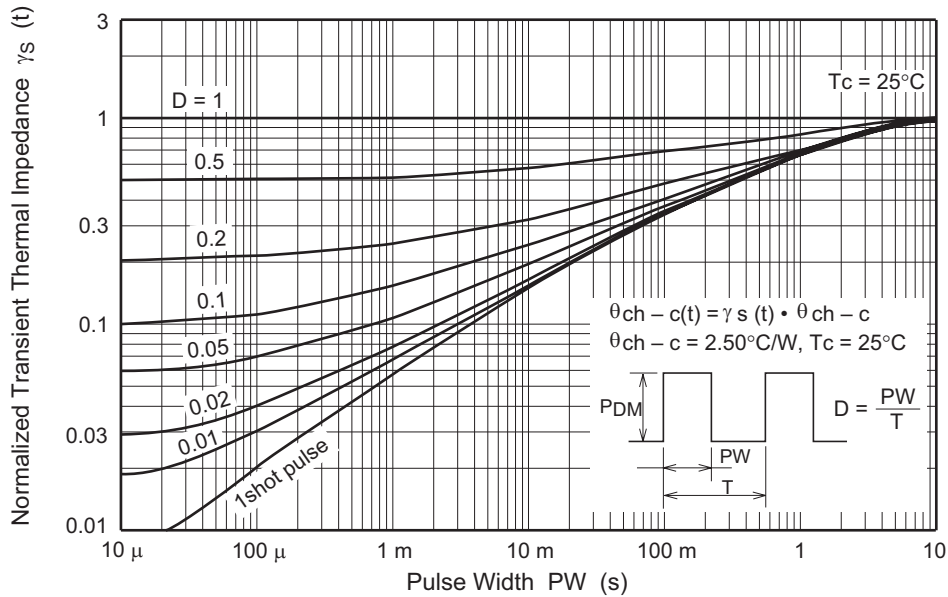




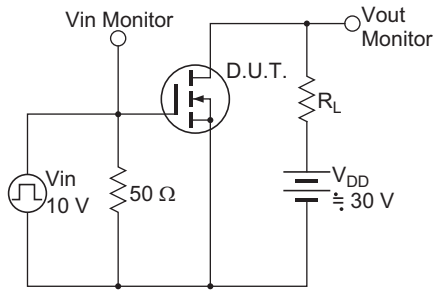
Reverse Drain Current vs. Source to Drain Voltage



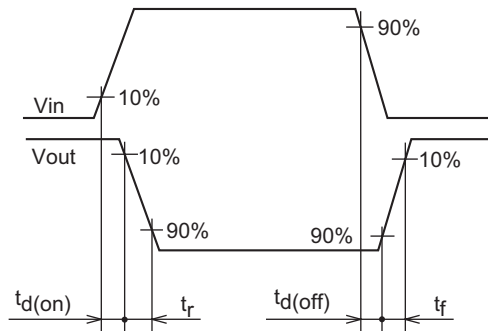
Normalized Transient Thermal Impedance vs. Pulse Width



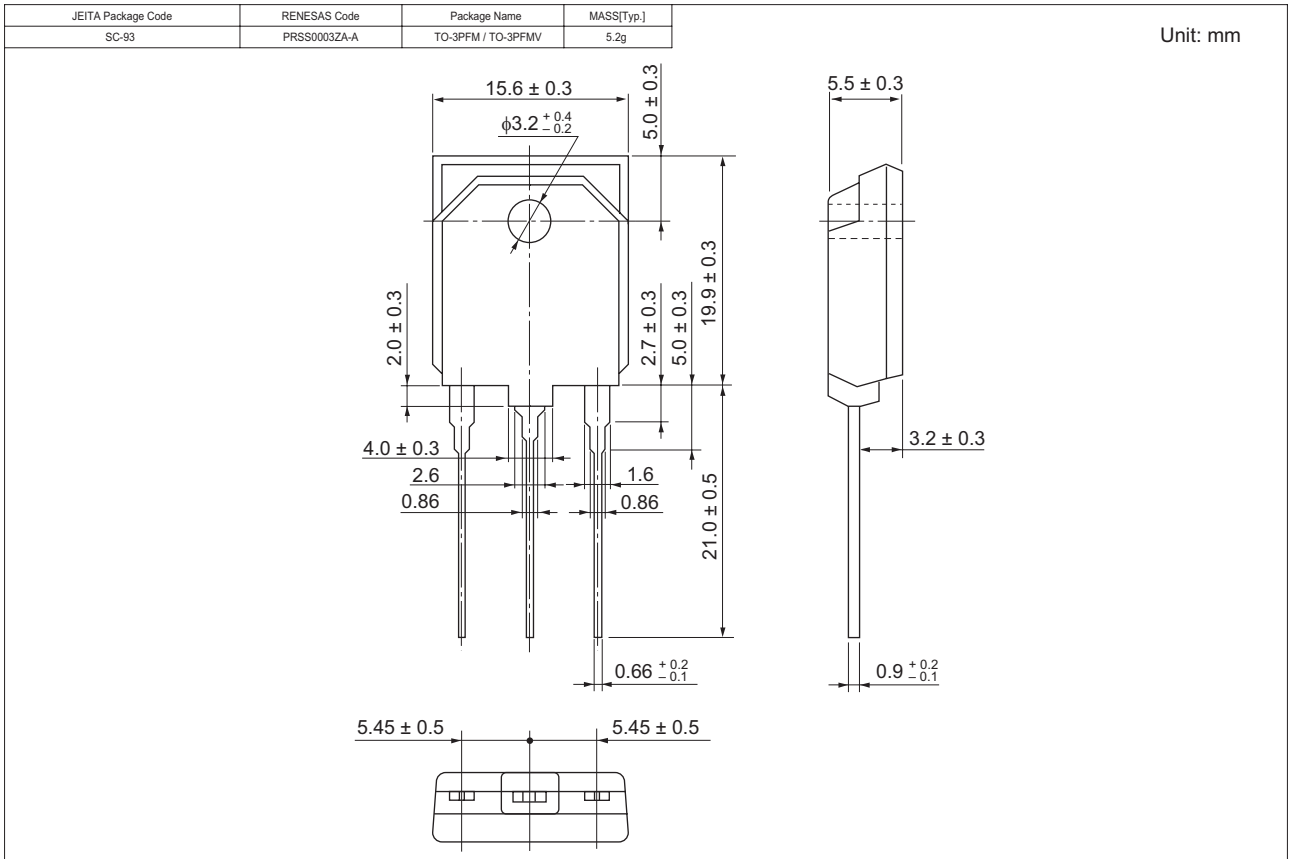
Switching Time Test Circuit



Waveforms



Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SK2225-E	360 pcs	Box (Tube)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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